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ABSOLUTE MAXIMUM RATINGS (Values are at T_A = 25°C unless otherwise noted) (Note 1)

Rating		Symbol	Value	Unit
Maximum Repetitive Reverse Voltage		V_{RRM}	100	V
Average Rectified Forward Current		I_O	200	mA
DC Forward Current		I_F	300	mA
Recurrent Peak Forward Current		I_f	400	mA
Non−repetitive Peak Forward Surge Current	Pulse Width = 1.0 s	I_{FSM}	1.0	A
	Pulse Width = 1.0 μs		4.0	A
Storage Temperature Range		T_{STG}	−65 to +200	°C
Operating Junction Temperature Range		T_J	−55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. These ratings are limiting values above which the serviceability of the diode may be impaired.

THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Power Dissipation	P_D	500	mW
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	300	°C

ELECTRICAL CHARACTERISTICS (Values are at T_A = 25°C unless otherwise noted) (Note 2)

Symbol	Parameter		Conditions	Min	Max	Unit
V_R	Breakdown Voltage		I_R = 100 μA	100		V
			I_R = 5.0 μA	75		V
V_F	Forward Voltage	914B / 4448	I_F = 5.0 mA	0.62	0.72	V
		916B	I_F = 5.0 mA	0.63	0.73	V
		914 / 916 / 4148	I_F = 10 mA		1.0	V
		914A / 916A	I_F = 20 mA		1.0	V
		916B	I_F = 20 mA		1.0	V
		914B / 4448	I_F = 100 mA		1.0	V
I_R	Reverse Leakage		V_R = 20 V		0.025	μA
			V_R = 20 V, T_A = 150°C		50	μA
			V_R = 75 V		5.0	μA

TYPICAL PERFORMANCE CHARACTERISTICS

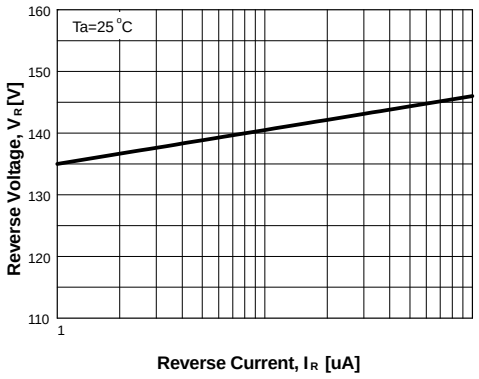
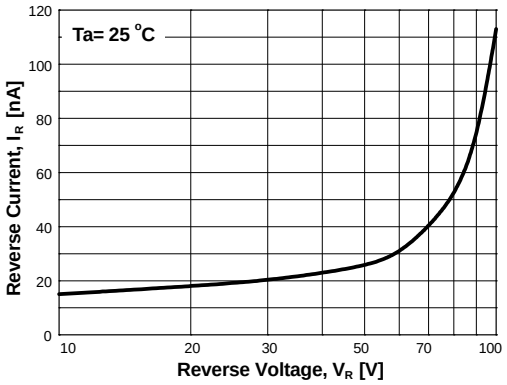


Figure 1. Reverse Voltage vs. Reverse Current
B_V – 1.0 to 100 μA



GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

TYPICAL PERFORMANCE CHARACTERISTICS

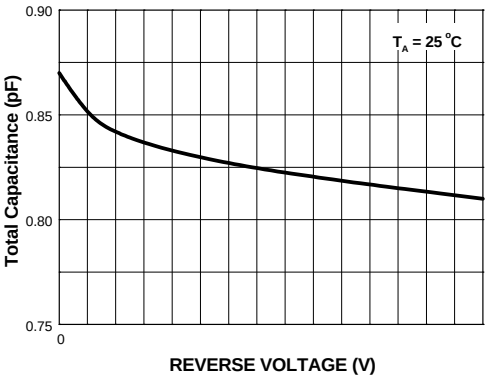


Figure 7. Total Capacitance

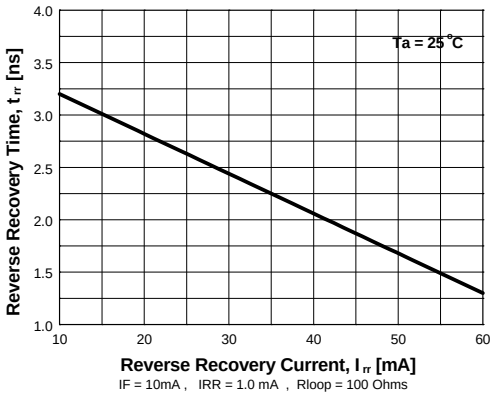
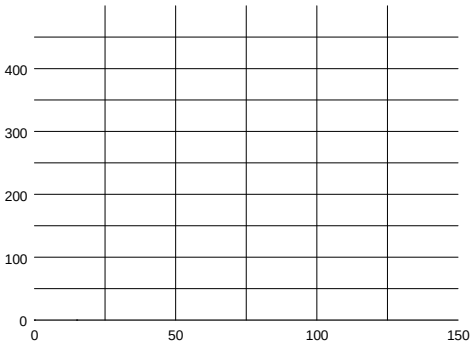


Figure 8. Reverse Recovery Time vs. Reverse Recovery Current



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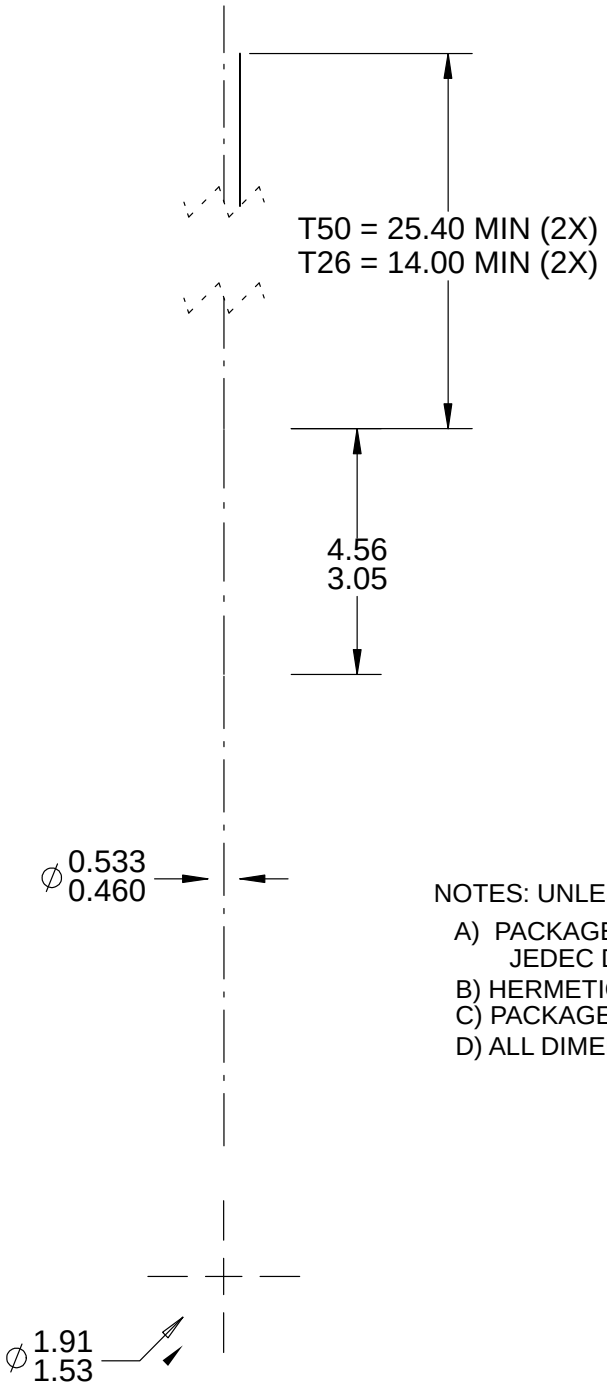
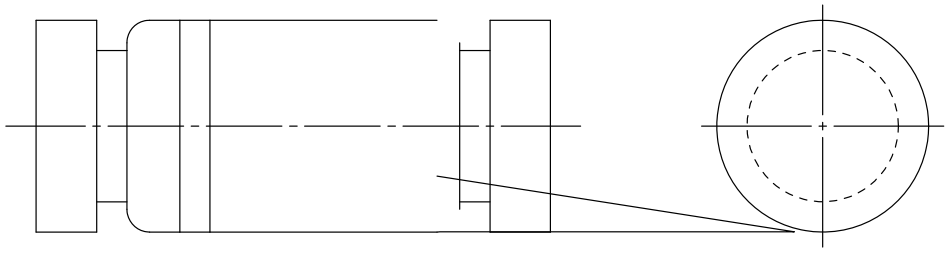


NOTES: UNLESS OTHERWISE SPECIFIED

A) PACKAGE STANDARD REFERENCE: JEDEC DO−204, VARIATION AH.
B) HERMETICALLY SEALED GLASS PACKAGE.
C) PACKAGE WEIGHT IS 0.137 GRAM.
D) ALL DIMENSIONS ARE IN MILLIMETERS.

MiniMELF / SOD 80
CASE 100AD
ISSUE O

DATE 30 APR 2012



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